

AMENDMENTS TO THE SPECIFICATION

Please replace the column labels in Table 10, page 17, as follows:

Sample	ArF Laser (193nm)		Inspection wavelength		Note
			248nm	365nm	
	Transmittance	Phase difference	Transmittance	Phase difference	
	n %	k deg.	n %	k deg.	

Please amend the paragraph spanning pages 21 and 22, as follows:

A double layer structure is adopted in the samples TS1 to TS4, TS6 and TS7 as show in Table 9 where a film of which the absorption is high and of which the chemical resistance properties are excellent is formed as the upper layer while a film of which the absorption is low and of which the chemical resistance properties are poor is formed as the lower layer. By using the double layer structure the transmittance for the inspection wavelength (365nm) is designed to be less than approximately 40%. This principle is the same as in background technology 2.

Please amend the third full paragraph on page 32, as follows:

In addition, since the ~~L/S~~ T/S distance is sufficiently large, the effects gained from reactive gases reaching the sputtering target become smaller so as to reduce oxidation and nitriding of the target and, thereby, factors of defect occurrence, such as particles of the mask or pinholes, can be avoided.